

# Organic Photodetectors

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Contributor: Jianhua Zhang

Organic photodetectors (OPDs) have gained increasing interest as they offer cost-effective fabrication methods using solution processes and a tunable spectral response range, making them particularly attractive for large area image sensors on lightweight flexible substrates. Carrier blocking layers engineering is very important to the high performance of OPDs that can select a certain charge carriers (holes or electrons) to be collected and suppress another carrier. Carrier blocking layers of OPDs play a critical role in reducing dark current, boosting their efficiency and long-time stability.

Keywords: organic photodetector ; carrier blocking layer ; energy alignment ; dark current ; efficiency

## 1. Introduction

Photodetectors can convert optical signals to electronic signals, which are widely applied in optical communication, environmental monitoring, cameras, smart phones, image sensing, and so on [1][2][3][4][5]. Compared to commercial photodetectors such as silicon (Si)- and indium gallium arsenide (InGaAs)-based photodetectors, OPDs are increasingly attractive for light sensing applications as they combine detection wavelength tenability, solution processability, and high photogeneration yield with low fabrication costs, lightweight, and flexibility [6][7]. The basic structure of OPDs generally includes two essentials parts: an active layer for light absorption and electrodes for the collection of charge carriers (electrons and holes). The working mechanism of OPDs is similar to that of organic photovoltaics (OPVs), which can be summarized as (i) the organic semiconductors absorb photons to generate excitons (electron-hole pair) and then the excitons diffuse to donor/acceptor interfaces; (ii) the excitons separate into electrons and holes driven by electric field force formed by extra applied bias; (iii) holes are transferred to the anode through the channels formed by the highest occupied molecular orbital (HOMO) of the donor, and electrons are transported to the cathode via the channels formed by the lowest unoccupied molecular orbital (LUMO) of the acceptor; (iv) the holes and electrons are collected by the corresponding electrode to generate photocurrent.

Continuously improving the high gain property, OPDs have achieved significant breakthroughs and rapid evolution in the last several decades, thanks to the developments of novel donor/acceptor materials, the innovations of the device structure, and interface engineering. Kang et al., reported high-detectivity green-selective all-polymer p-n junction photodetectors by engineering the  $\pi$ -conjugation networks and insulating properties of p- and n-type polymers [8]. Zhang et al., achieved planar heterojunction (PHJ) OPDs based on the medium-band gap fullerene C<sup>60</sup> and a new low-band gap fused-ring non-fullerene acceptor bilayer structure for a tunable spectral response [9]. Nie reported that aligned nanofibers (ANs) prepared by electrostatic spinning technology as an interfacial layer can significantly enhance the performance of inverted OPDs [10]. Due to the lower relative permittivity ( $\epsilon_r \approx 3-4$ ) of organic in comparison with inorganic materials [11], excitons with a relatively high binding energy of  $\approx 0.35-0.5$  eV are generated after light absorption, rather than free electrons and holes. Thus, the active layer of OPDs is often based on a bulk heterojunction (BHJ) architecture that comprises finely bicontinuous and interpenetrative networks of electron donor and acceptor phases, in which this structure facilitates exciton dissociation and charge transport to the relevant electrodes [12].

## 2. Carrier Blocking Layer Materials and Application in Organic Photodetectors

Different types of blocking layer materials have been demonstrated to play a critical role in OPDs. At present, the interface layer materials in organic solar cells and OPDs have great similarities. However, due to the different working mechanisms of devices, not all materials can be used in OPDs. Therefore, more research and optimization of these materials should be carried out for OPDs. From Table 1 and Table 2, we can ascertain the development of OPDs in hole and electron blocking layer materials in recent years, respectively. However, more efforts are needed to promote their applications and to propose new materials for OPDs.

**Table 1.** Survey of the main characteristics of OPD employing materials such as HBLs.

| Materials | Device Structure                                   | $J_d$ (A cm <sup>-2</sup> ) | $EQE$ (%)           | $D^*$ (Jones)         | $R$ (A W <sup>-1</sup> ) | Measurement Conditions                    | Ref  |
|-----------|----------------------------------------------------|-----------------------------|---------------------|-----------------------|--------------------------|-------------------------------------------|------|
| BCP       | ITO/PEDOT:PSS/active layer/BCP/Al                  | $1.1 \times 10^{-9}$        | -                   | $1.4 \times 10^{12}$  | 0.068                    | -2 V, @ 800 nm                            | [13] |
|           | ITO/TPBi/MoO <sub>3</sub> /C70/active layer/BCP/Al | $2.2 \times 10^{-2}$        | 68,927 <sub>1</sub> | $2.2 \times 10^{12}$  | 188                      | -6 V, @ 345 nm                            | [14] |
|           | ITO/PEDOT:PSS/active layer/BCP/Al                  | $1.3 \times 10^{-5}$        | 2170                | $8.3 \times 10^{11}$  | 6.39                     | -15 V, @ 360 nm                           | [15] |
| Bphen     | ITO/TAPC:MoO <sub>3</sub> /active layer/Bphen/Ag   | $1.11 \times 10^{-9}$       | 41.8                | $6.43 \times 10^{12}$ | 0.121                    | -3 V, @ 360 nm                            | [16] |
|           | ITO/PEDOT:PSS/active layer/BCP/Ag                  | $4.82 \times 10^{-4}$       | -                   | $3.7 \times 10^{11}$  | -                        | -1.5 V, @ 350 nm, 0.5 mW cm <sup>-2</sup> | [17] |
|           | ITO/MoO <sub>3</sub> /CuI/active layer/Bphen/Al    | $\sim 10^{-2}$              | 400                 | $10^{12}$             | -                        | -8 V, @ 870 nm                            | [18] |
|           | ITO/PEDOT:PSS/active layer/BCP/Ag                  | $\sim 10^{-5}$              | 43.78               | $2.67 \times 10^{12}$ | 0.25                     | @ 710 nm                                  | [19] |
|           | ITO/TAPC/active layer/BCP/Ag                       | $1.15 \times 10^{-9}$       | 74.6                | $4.14 \times 10^{13}$ | 0.439                    | -2 V, @ 730 nm                            | [20] |
| PEIE      | ITO/PEIE/active layer/MoO <sub>3</sub> /Ag         | $7.7 \times 10^{-9}$        | 60                  | $4.8 \times 10^{12}$  | 0.24                     | -1.5 V, @ 546 nm                          | [21] |
|           | ITO/PEIE/active layer/Al                           | $4 \times 10^{-5}$          | 12,000              | $2.27 \times 10^{12}$ | 54                       | -0.8 V, @ 530 nm                          | [22] |
|           | ITO/PEIE/active layer/Au                           | $7.7 \times 10^{-10}$       | -                   | $2.2 \times 10^{13}$  | 0.32                     | -2 V, @ 629 nm                            | [23] |
|           | ITO/PEIE/active layer/Al                           | $2.77 \times 10^{-6}$       | 3200                | $1.04 \times 10^{12}$ | 14.25                    | -1 V, @ 550 nm                            | [24] |
|           | PEDOT:PSS/PEIE/active layer/PEDOT:PSS              | $1.5 \times 10^{-10}$       | 55                  | $3.45 \times 10^{13}$ | -                        | -5 V, @ 530 nm                            | [25] |
| PFN       | ITO/PFN/active layer/Ag                            | $5.10 \times 10^{-4}$       | 67.09               | $2.47 \times 10^{12}$ | 0.37                     | -0.5 V, @ 680 nm                          | [26] |
|           | ITO/PFN/active layer/Al                            | $\sim 10^{-3}$              | 650                 | $1.76 \times 10^{12}$ | 8.7                      | -15 V, @ 520 nm                           | [27] |
|           | ITO/PFN/active layer/Al                            | $1.92 \times 10^{-8}$       | 208.11              | $9.1 \times 10^{12}$  | 0.921                    | -0.5 V, @ 550 nm                          | [28] |
|           | ITO/PEDOT:PSS/active layer/PFN-Br/Ag               | $\sim 10^{-8}$              | 65                  | $10^{13}$             | -                        | -10 V, @ 860 nm                           | [29] |
|           | ITO/PEDOT:PSS/active layer/PFN-Br/Al               | $4.85 \times 10^{-10}$      | 56                  | $2.61 \times 10^{13}$ | 0.33                     | -0.1 V, 720 nm                            | [6]  |
| PEI       | PEDOT:PSS/PEI/active layer/PEDOT:PSS/PEDOT:PSS     | $\sim 10^{-7}$              | 65                  | -                     | -                        | -4 V                                      | [30] |
|           | PEDOT:PSS/PEI/active layer/Poly-PT/PEDOT:PSS       | $\sim 10^{-7}$              | 65                  | $2.2 \times 10^{12}$  | -                        | -1 V, @ 505 nm                            | [31] |
|           | PEDOT:PSS/PEI/active layer/PEDOT:PSS               | $5.7 \times 10^{-8}$        | 46                  | $3.35 \times 10^{12}$ | -                        | -1 V, @ 525 nm                            | [32] |

| Materials                       | Device Structure                                               | $J_d$ (A cm <sup>-2</sup> ) | $EQE$ (%) | $D^*$ (Jones)          | $R$ (A W <sup>-1</sup> ) | Measurement Conditions  | Ref  |
|---------------------------------|----------------------------------------------------------------|-----------------------------|-----------|------------------------|--------------------------|-------------------------|------|
| C <sub>60</sub>                 | ITO/PEDOT:PSS/active layer/C <sub>60</sub> /Al                 | $8 \times 10^{-10}$         | 60        | $\sim 10^{13}$         | -                        | -1 V, @ 532 nm          | [33] |
|                                 | ITO/PEDOT:PSS/active layer/C <sub>60</sub> /Al                 | $1.1 \times 10^{-10}$       | 67.1      | $9.2 \times 10^{12}$   | 0.38                     | -1 V, @ 700 nm          | [34] |
|                                 | ITO/ZnO/active layer/MoO <sub>3</sub> /Ag                      | $6.51 \times 10^{-8}$       | $\sim 70$ | $2.58 \times 10^{11}$  | 0.48                     | -0.1 V, @ 700 nm        | [35] |
|                                 | Ag/ZnO/active layer/PEDOT:PSS                                  | $\sim 10^{-10}$             | -         | $2 \times 10^{12}$     | 0.3                      | -1 V, @ 532 nm          | [36] |
|                                 | ITO/ZnO/active layer/MoO <sub>3</sub> /Al                      | $3.9 \times 10^{-9}$        | 140,000   | $6.3 \times 10^{12}$   | -                        | -0.5 V, @ 680 nm        | [37] |
|                                 | ITO/ZnO/PEIE/active layer/MoO <sub>3</sub> /Ag                 | $8.075 \times 10^{-6}$      | 62        | $3.749 \times 10^{12}$ | 0.281                    | 2 V, @ 680 nm           | [38] |
|                                 | PEDOT:PSS/ZnO/PEIE/active layer/PEDOT:PSS                      | $2.11 \times 10^{-8}$       | $\sim 40$ | $\sim 10^{11}$         | $\sim 0.17$              | 0 V, @ 700 nm           | [39] |
| TiO <sub>2</sub>                | ITO/TiO <sub>2</sub> /active layer/MoO <sub>3</sub> /Ag        | $\sim 10^{-7}$              | -         | $\sim 10^{12}$         | 0.022                    | 0 V, @ 350 nm           | [40] |
|                                 | ITO/TiO <sub>2</sub> /active layer/Al                          | $1.09 \times 10^{-7}$       | 113       | $1.9 \times 10^{12}$   | 0.5                      | -1 V, @ 550 nm          | [41] |
|                                 | ITO/TiO <sub>2</sub> /active layer/MoO <sub>3</sub> /Al        | $\sim 10^{-9}$              | 94.22     | $2.93 \times 10^{13}$  | -                        | 0 V, @ 690 nm           | [10] |
| SnO <sub>2</sub>                | ITO/SnO <sub>2</sub> /active layer/Al                          | $2.89 \times 10^{-4}$       | 1430      | $2.29 \times 10^{13}$  | 6.97                     | -1 V, @ 625 nm          | [42] |
|                                 | ITO/SnO <sub>2</sub> /active layer/MoO <sub>3</sub> /Ag        | $\sim 10^{-9}$              | $\sim 70$ | $5.82 \times 10^{12}$  | -                        | -1 V, @ 900 nm          | [43] |
| Cs <sub>2</sub> CO <sub>3</sub> | ITO/PEDOT:PSS/active layer/Cs <sub>2</sub> CO <sub>3</sub> /Al | $2.1 \times 10^{-8}$        | >100      | $3 \times 10^{12}$     | -                        | -3 V, @ 450 nm          | [44] |
| LiF                             | ITO/PEDOT:PSS/active layer/LiF/Al                              | $1.7 \times 10^{-8}$        | -         | -                      | 0.004                    | -3 V, @ solar simulator | [45] |
|                                 | ITO/PEDOT:PSS/active layer/LiF/Al                              | $2.7 \times 10^{-7}$ (-1 V) | 5600      | -                      | 15.9                     | -40 V, @ 360 nm         | [46] |

<sup>1</sup> Graphene oxide functionalized with cysteine.

**Table 2.** Survey of the main characteristics of OPD-employing materials such as EBLs.

| Materials      | Device Structure                    | $J_d$ (A cm <sup>-2</sup> ) | $EQE$ (%) | $D^*$ (Jones)         | $R$ (A W <sup>-1</sup> ) | Measurement Conditions | Ref  |
|----------------|-------------------------------------|-----------------------------|-----------|-----------------------|--------------------------|------------------------|------|
| TFB            | ITO/TFB/active layer/Al             | $2 \times 10^{-8}$          | 35        | $3.34 \times 10^{12}$ | -                        | -5 V, @ 900 nm         | [47] |
|                | PEDOT:PSS/TFB/active layer/F8TBT/Al | $4 \times 10^{-9}$          | 20        | -                     | -                        | -0.5 V, @ 650 nm       | [48] |
|                | ITO/PEDOT:PSS/TFB/active layer/Al   | $8 \times 10^{-9}$          | 9         | -                     | -                        | -0.5 V, @ 530 nm       | [49] |
|                | ITO/TFB/active layer/Al             | $3.4 \times 10^{-11}$       | 82        | $2.19 \times 10^{13}$ | 0.44                     | -5 V, @ 660 nm         | [50] |
| TIPS pentacene | ITO/TIPS pentacene/active layer/Al  | $1 \times 10^{-9}$          | 52        | $1.44 \times 10^{13}$ | -                        | -5 V, @ 610 nm         | [51] |
|                | ITO/TIPS pentacene/active layer/Al  | $9 \times 10^{-10}$         | 80        | $1.63 \times 10^{13}$ | -                        | -5 V, @ 530 nm         | [52] |

| Materials                     | Device Structure                                                                              | $J_d$ (A cm <sup>-2</sup> ) | $EQE$ (%)          | $D^*$ (Jones)           | $R$ (A W <sup>-1</sup> ) | Measurement Conditions             | Ref  |
|-------------------------------|-----------------------------------------------------------------------------------------------|-----------------------------|--------------------|-------------------------|--------------------------|------------------------------------|------|
| PEDOT:PSS                     | ITO/PEDOT:PSS/active layer/Al                                                                 | $\sim 10^{-3}$              | $\sim 250$         | $\sim 6 \times 10^{11}$ | 0.93                     | -10 V, @ 400 nm                    | [53] |
|                               | ITO/PEDOT:PSS/active layer/Al                                                                 | $2.68 \times 10^{-6}$       | $3.92 \times 10^5$ | $1.4 \times 10^{11}$    | 46.1                     | -25 V, @ 510 nm                    | [54] |
|                               | ITO/PEDOT:PSS/active layer/Al                                                                 | $\sim 10^{-7}$              | 2000               | $\sim 10^{11}$          | $\sim 0.4$               | -50 V, @ 510 nm                    | [55] |
|                               | ITO/PEDOT:PSS+ GO-Cys <sup>-1</sup> /active layer/Al                                          | $\sim 10^{-10}$             | -                  | $5.7 \times 10^{12}$    | $\sim 0.15$              | -0.1 V, @ 620 nm                   | [56] |
| P3HT                          | ITO/PEIE/active layer/P3HT/MoO <sub>3</sub> /Al                                               | $\sim 1.5 \times 10^{-9}$   | -                  | $4.15 \times 10^{12}$   | 0.19                     | -0.1 V, @ 525 nm                   | [57] |
|                               | ITO/ZnO/active layer/P3HT/MoO <sub>3</sub> /Al                                                | $1.1 \times 10^{-8}$        | 70                 | $3.0 \times 10^{12}$    | 0.34                     | -3 V, @ 630 nm                     | [58] |
|                               | ITO/ZnO/active layer/P3HT/Ag                                                                  | $9 \times 10^{-5}$          | -                  | $6.59 \times 10^{10}$   | 0.214                    | -2 V, @ 630 nm                     | [59] |
| NiO <sub>x</sub>              | ITO/NiO <sub>x</sub> /active layer/Yb/Ag                                                      | $\sim 10^{-8}$              | 53.39              | $2.15 \times 10^{12}$   | 0.253                    | -1 V, @ 525 nm                     | [60] |
|                               | ITO/NiO <sub>x</sub> /active layer/ZnO/Ag                                                     | $3.4 \times 10^{-8}$        | $\sim 52$          | $1.2 \times 10^{12}$    | 0.25                     | -1 V, @ 600 nm                     | [61] |
|                               | ITO/ZnO:Al/active layer/NiO <sub>x</sub> /Ag                                                  | $1.13 \times 10^{-7}$       | -                  | $3.86 \times 10^{12}$   | 0.74                     | -5 V, @ 525 nm                     | [62] |
|                               | ITO/ZnO:Al/active layer/NiO <sub>x</sub> /Ag                                                  | $8.09 \times 10^{-8}$       | 81.93              | $2.15 \times 10^{12}$   | 0.35                     | -5 V, @ 525 nm                     | [63] |
| MoO <sub>3</sub>              | ITO/ZnO/active layer/MoO <sub>3</sub> /Ag                                                     | $5.9 \times 10^{-9}$        | -                  | $3.04 \times 10^{12}$   | -                        | -3 V, @ 650 nm                     | [64] |
|                               | Al/ZnO/active layer/MoO <sub>3</sub> /Ag/MoO <sub>3</sub>                                     | $2.95 \times 10^{-7}$       | 31                 | $4.49 \times 10^{11}$   | 0.14                     | -1.5 V, @ 650 nm                   | [65] |
|                               | Al/PCBM/active layer/MoO <sub>3</sub> /Ag/MoO <sub>3</sub>                                    | $1 \times 10^{-9}$          | 30                 | $6 \times 10^{12}$      | -                        | -1 V, @ 500 nm                     | [66] |
| V <sub>2</sub> O <sub>5</sub> | ITO/PEDOT:PSS + V <sub>2</sub> O <sub>5</sub> /active layer/V <sub>2</sub> O <sub>5</sub> /Al | $5.53 \times 10^{-3}$       | -                  | -                       | -                        | -1 V, @ (AM 1.5 G) solar simulator | [67] |
| CuSCN                         | ITO/CuSCN/active layer/LiF/Al                                                                 | $2.7 \times 10^{-10}$       | 57.2               | $4.4 \times 10^{13}$    | 0.4                      | -0.1 V, @ 870 nm                   | [68] |
|                               | ITO/CuSCN/active layer/BCP/Mg:Ag                                                              | $1 \times 10^{-8}$          | -                  | -                       | -                        | -1 V                               | [69] |

- (1) Organic interface materials in OPDs are expected to be used in future flexible wearable electronic devices, and further research is needed. However, it is necessary to develop new strategies to solve the problem that they are orthogonal to the solvent of the organic active layer according to the device structure.
- (2) Inorganic materials have also been studied extensively in OPDs because of their high stability. However, the particle size of the material needs to be further reduced, and there are still relatively few p-type inorganic nanomaterials for EBLs. How to achieve the preparation of high-quality inorganic blocking layers at low temperature or even room temperature is the focus of our attention.
- (3) Doping is one of the straightforward ways to modify the carrier blocking layer. The method of inorganic nanoparticle doping in organic interface materials is expected to be used in the future research of OPD because it combines the advantages of the two types of materials.

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